

**REMARKS**

Claims 1-3 and 5-28 are pending in this application, of which claims 1, 21-23, 26 and 27 have been amended. No new claims have been added.

(1) Claims 1-3 and 5-28 were rejected under 35 U.S.C. §103(a) as being unpatentable over Ishibashi et al. (U.S. Patent No. 6,579,657) in view of Kanda et al. (JP2001-019860).

(i) Claims 1, 21, 23, 26 and 27 have been amended to delete the “alcohol surfactant” and “secondary alcohol ethoxylate surfactant.” The surfactants taught by Kanda et al. are an acetylene alcohol, an acetylene glycol, a polyethoxylate of an acetylene alcohol, and a polyethoxylate of an acetylene glycol. Kanda et al. do not teach or suggest the other surfactants. Please see the abstract and paragraphs [0009]-[0010]. Thus, even a combination of the cited references does not make the invention of the amended claims.

(ii) Claims 1, 21, 23, 26 and 27 have been also amended to incorporate the limitation of thickening the resist pattern formed of an ArF resist. The basis of the amendment is found at page 3, line 12 to page 6, line 10; page 37, last line 4 to 38, line 9; and etc.

None of the cited references teaches thickening a resist pattern formed by using an ArF resist. In Examples of Ishibashi et al., the resist patterns formed by using an i ray resist, a KrF resist and an EB resist (col. 12, line 55 to col. 14, line 16) were thickened. In Kanda et al., the

resist patterns formed by using an i resist and a KrF resist were thickened (paragraphs [0023]-[0024]). There is no actual data disclosed in the cited references that the disclosed composition can be used for thickening a resist pattern formed by using an ArF resist. Neither of the cited references teaches a resist pattern thickening material for thickening a resist pattern formed by using an ArF resist.

Even if the Examiner construes that Ishibashi et al. inherently teach an ArF resist, it is believed that the invention of the composition for thickening a resist pattern formed of an ArF resist was not completed at the time when Ishibashi et al. was filed, at least because there is no actual reduction of the invention for the composition for thickening a resist pattern formed of an ArF resist. It is not obvious to one skilled in the art to modify the incomplete invention of Ishibashi et al. to complete by referring to the teachings of the second reference.

On the other hand, the material of the present invention, as specifically recited in the claims, can efficiently thicken the resist pattern formed of ArF resist, as shown in the description and Tables 1-3 at pages 37-41 of the specification.

Thus, the present invention is unobvious over the cited references. Reconsideration of the rejection is respectfully requested.

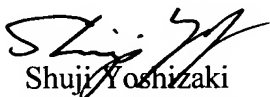
Amendment after Final  
Application No. 10/623,679  
Attorney Docket No. 030891

(2) In view of the aforementioned amendments and accompanying remarks, Applicants submit that the claims, as herein amended, are in condition for allowance. Applicants request such action at an early date.

If the Examiner believes that this application is not now in condition for allowance, the Examiner is requested to contact Applicants' undersigned representative at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

If this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,  
**WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP**

  
Shuji Yoshizaki  
Limited Recognition  
Telephone: (202) 822-1100  
Facsimile: (202) 822-1111

SY/mt  
Attachment: Limited Recognition